

What is claimed is:

1. A method of manufacturing a semiconductor wafer, comprising the steps of:

5 annealing a wafer at a low temperature in order to form a nucleation site at a region deep into the wafer; and

performing rapid thermal annealing process so that oxygen precipitation material, metallic impurity, etc. is trapped in the nucleation site

10 2. The method as claimed in claim 1, wherein the low-temperature annealing process is performed at a temperature of 650 ~ 850 °C under nitrogen (N₂) atmosphere for 3 ~ 10 hours.

3 The method as claimed in claim 1, wherein the rapid thermal
15 annealing process is performed at a temperature of 1000 ~ 1200 °C under nitrogen (N₂) atmosphere for 10 seconds ~ 5 minutes.

4 The method as claimed in claim 1, wherein in the rapid thermal
annealing process, a step-up rate is 30 ~ 200 °C/sec, a cooling rate is 200 ~ 100 °C
20 /sec and the flux of nitrogen (N₂) is 1 ~ 20slpm.

5 The method as claimed in claim 1, further comprising the step of before the low-temperature annealing process is implemented, performing high-temperature annealing process in order to diffuse oxygen existing on the surface of

the wafer toward the outside.

6. The method as claimed in claim 5, wherein the low-temperature annealing process is performed at a temperature of 1000 ~ 1200°C under dry
5 oxygen (O₂) atmosphere for 1 ~ 2 hours.